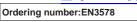
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PNP/NPN Epitaxial Planar Silicon Transistors

2SA1770/2SC4614

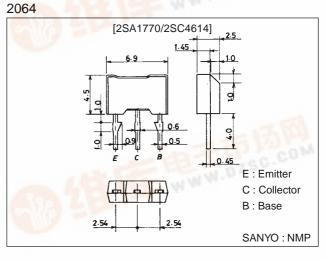
High-Voltage Switching Applications

Features

- · Adoption of MBIT process.
- · High breakdown voltage and large current capacity.

Package Dimensions

unit:mm



():2SA1770

Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|---------------------|-------------|------|
| Collector-to-Base Voltage | VCBO | | (–)180 | V |
| Collector-to-Emitter Voltage | VCEO | | (–)160 | V |
| Emitter-to-Base Voltage | VEBO | | (–)6 | V |
| Collector Current | IC | and the | ()1.5 | A |
| Colletor Current (Pulse) | ICP | A REAL PROPERTY AND | (–)2.5 | A |
| Collector Dissipation | PC | A REAL PROPERTY | 1 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | –55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | | Ratings | | |
|---|----------------------|---|------|---------|--------|------|
| | | | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =(-)120V, I _E =0 | | | (–)1 | μA |
| Emitter Cutoff Current | IEBO | V _{EB} =(-)4V, I _C =0 | | | (–)1 | μA |
| DC Current Gain | h _{FE} 1 | V _{CE} =(-)5V, I _C =(-)100mA | 100* | 1 | 400* | 6.0 |
| | h _{FE} 2 | V _{CE} =(-)5V, I _C =(-)10mA | 80 | - 5 | 7 2 4 | 10% |
| Gain-Bandwidth Product | fT | V _{CE} =(-)10V, I _C =(-)50mA | - 12 | 120 | SU | MHz |
| Output Capacitance | Cob | V _{CB} =(-)10V, f=1MHz | W LL | (22)14 | | pF |
| Collector-to-Emitter Saturation Voltage | V _{CE(sat)} | I _C =(-)500mA, I _B =(-)50mA | | (–200) | (–500) | mV |
| | | | | 130 | 450 | mV |
| Base-to-Emitter Saturation Voltage | V _{BE(sat)} | IC=(-)500mA, IB=(-)50mA | | (–)0.85 | (–)1.2 | V |

Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

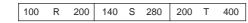
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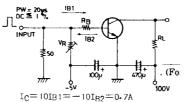
2SA1770/2SC4614

| Parameter | Symbol | Conditions | | Ratings | | |
|--|-----------------------|--|--------|---------|-----|------|
| | Symbol | | min | typ | max | Unit |
| Collector-to-Base Breakdown Voltage | V _(BR) CBO | I _C =(-)10μA, I _E =0 | (–)180 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | I _C =(−)1mA, R _{BE} =∞ | (–)160 | | | V |
| Emitter-to-Base Breakdown Voltage | V _{(BR)EBO} | I _E =(-)10μΑ, I _C =0 | (–)6 | | | V |
| Turn-ON Time | ton | See specified Test Circuit | | (40)40 | | ns |
| Storage Time | tstg | See specified Test Circuit | | (0.7) | | μs |
| | | | | 1.2 | | μs |
| Fall Time | t _f | See specified Test Circuit | | (40)80 | | ns |

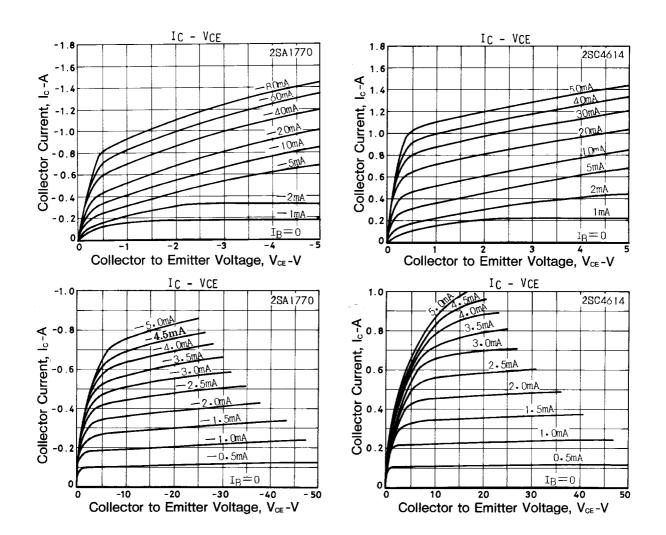
 \ast ; The 2SA1770/2SC4614 are classified by 100mA h_{FE} as follows :



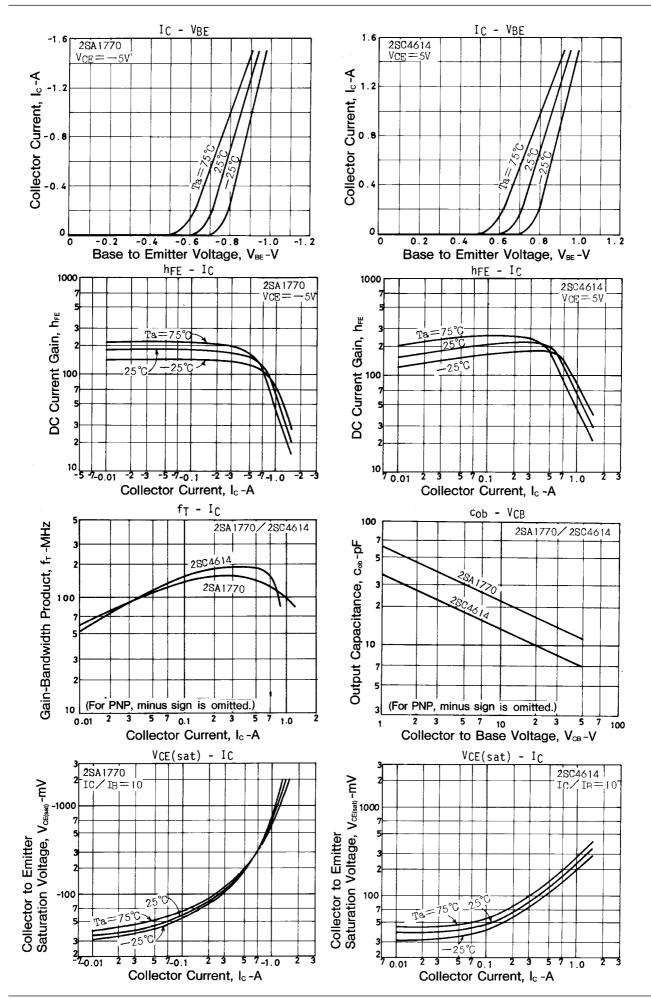
Switching Time Test Circuit



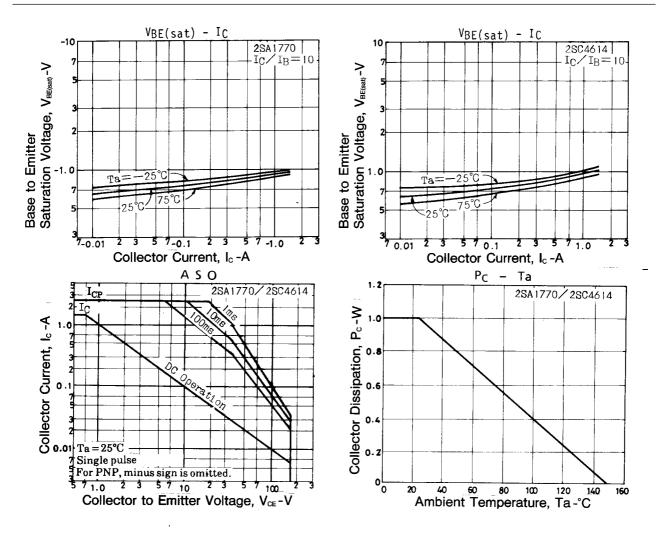
Unit (resistance : Ω , capacitance : F)



2SA1770/2SC4614



2SA1770/2SC4614



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